

WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:

a laser emission part for emitting a laser beam;

5 a laser reception part for receiving a backward beam of the laser beam reflected by an irradiation object;

a polarization hologram for transmitting the laser beam directed from the laser emission part to the irradiation object as a forward beam without diffracting the beam, and diffracting a backward beam of the laser beam, which is a return beam of the forward beam that has been reflected by the irradiation object, so that the backward beam is deflected from a direction directed toward the laser emission part and further directed toward the laser reception part; and

15 a three-beam diffraction grating for dividing a holographic diffracted beam, which results from the diffraction of the backward beam by the polarization hologram, into three beams and for letting the beam incident on the laser reception part.

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2. The semiconductor laser device according to Claim 1, wherein

the polarization hologram and the three-beam diffraction grating are integrated together.

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3. The semiconductor laser device according to Claim 1, wherein

the three-beam diffraction grating is so positioned that the forward beam directed from the laser emission part toward the irradiation object is inhibited from being incident on the three-beam diffraction grating.

4. The semiconductor laser device according to Claim 1, wherein

the laser reception part includes a first photoreception part for receiving a +1st-order diffracted beam derived from the polarization hologram, and a second photoreception part for receiving a -1st-order diffracted beam derived from the polarization hologram.

5. The semiconductor laser device according to Claim 1, wherein

the three-beam diffraction grating varies in diffraction efficiency depending on positions in a grating-extension direction along which the grating extends.

6. The semiconductor laser device according to Claim 5, wherein

in the three-beam diffraction grating, a land width to groove width ratio of land portions and groove

portions which constitute the grating continuously varies along the grating-extension direction.

7. The semiconductor laser device according to Claim
5 5, wherein

 in the three-beam diffraction grating, groove depth of the grating continuously varies along the grating-extension direction.

10 8. The semiconductor laser device according to Claim
 5, wherein

 in the three-beam diffraction grating, groove depth of the grating varies stepwise along the grating-extension direction.

15 9. An optical pickup device comprising:
 a laser emission part for outputting a laser beam;

 a laser reception part for receiving a backward
20 beam of the laser beam reflected by an optical disk;

 a polarization hologram for transmitting the laser beam directed from the laser emission part to the optical disk as a forward beam without diffracting the beam, and diffracting a backward beam of the laser beam,
25 which is a return beam of the forward beam that has been

reflected by the optical disk, so that the backward beam is deflected from a direction directed toward the laser emission part and further directed toward the laser reception part;

5 a 1/4 wave plate corresponding to a wavelength of the laser beam

 an objective lens for focusing the laser beam onto the optical disk; and

 a three-beam diffraction grating for dividing a
10 holographic diffracted beam, which results from the diffraction of the backward beam by the polarization hologram, into three beams and for letting the beam incident on the laser reception part.